Mircea D Guina

List of Publications by Citations

345 papers	3,941 citations	30 h-index	41 g-index
468 ext. papers	4,896 ext. citations	3.1 avg, IF	5.35 L-index

#	Paper	IF	Citations
345	Semiconductor disk lasers for the generation of visible and ultraviolet radiation. *Laser and Photonics Reviews*, **2009**, 3, 407-434	8.3	118
344	Tunable Raman Soliton Source Using Mode-Locked TmHo Fiber Laser. *IEEE Photonics Technology Letters*, **2007**, 19, 934-936	2.2	109
343	Optically pumped VECSELs: review of technology and progress. *Journal Physics D: Applied Physics*, **2017**, 50, 383001	3	86
342	Subpicosecond thin-disk laser oscillator with pulse energies of up to 25.9 microjoules by use of an active multipass geometry. *Optics Express*, **2008**, 16, 20530-9	3.3	77
341	Nanostructured broadband antireflection coatings on AlInP fabricated by nanoimprint lithography. *Solar Energy Materials and Solar Cells*, **2010**, 94, 1845-1848	6.4	64
340	High-efficiency 20 W yellow VECSEL. *Optics Express*, **2014**, 22, 6372-80	3.3	60
339	High-pulse-energy passively Q-switched quasi-monolithic microchip lasers operating in the sub-100-ps pulse regime. *Optics Letters*, **2007**, 32, 2115-7	3	53
338	High-power semiconductor disk laser based on InAsGaAs submonolayer quantum dots. *Applied Physics Letters*, **2008**, 92, 101123	3.4	51
337	Variation of lattice constant and cluster formation in GaAsBi. *Journal of Applied Physics*, **2013**, 114, 243504	2.5	44
336	GaSb-based SESAM mode-locked Tm:YAG ceramic laser at 2 μm. *Optics Express*, **2015**, 23, 1361-9	3.3	40
335	SESAM mode-locked red praseodymium laser. *Optics Letters*, **2014**, 39, 6939-41	3	40
334	Optically-pumped dilute nitride spin-VCSEL. *Optics Express*, **2012**, 20, 3550-5	3.3	40
333	SESAM mode-locked Tm:CALGO laser at 2 μm. *Optical Materials Express*, **2016**, 6, 131	2.6	40
332	Formation and phase transformation of Bi-containing QD-like clusters in annealed GaAsBi. *Nanotechnology*, **2014**, 25, 205605	3.4	39
331	Passively Q-switched Tm3+, Ho3+-doped silica fiber laser using a highly nonlinear saturable absorber and dynamic gain pulse compression. *Optics Express*, **2008**, 16, 22058-63	3.3	39
330	Composition dependent growth dynamics in molecular beam epitaxy of GaInNAs solar cells. *Solar Energy Materials and Solar Cells*, **2014**, 124, 150-158	6.4	38
329	Modelocked GaSb disk laser producing 384 fs pulses at 2 [micro sign]m wavelength. *Electronics Letters*, **2011**, 47, 454	1.1	36

328	Sub-10 optical-cycle passively mode-locked Tm:(LuSc)O ceramic laser at 2 μm. *Optics Express*, **2018**, 26, 10299-10304	3.3	34
327	Quantum-dot semiconductor disk lasers. *Journal of Crystal Growth*, **2008**, 310, 5182-5186	1.6	34
326	1-W antimonide-based vertical external cavity surface emitting laser operating at 2-microm. *Optics Express*, **2006**, 14, 6479-84	3.3	34
325	Moth-eye antireflection coating fabricated by nanoimprint lithography on 1 eV dilute nitride solar cell. *Progress in Photovoltaics: Research and Applications*, **2013**, 21, 1158-1162	6.8	33
324	Mode-locking of 2 μm Tm,Ho:YAG laser with GaInAs and GaSb-based SESAMs. *Optics Express*, **2013**, 21, 4311-8	3.3	32
323	Oxidized In-containing III-V(100) surfaces: Formation of crystalline oxide films and semiconductor-oxide interfaces. *Physical Review B*, **2011**, 83,	3.3	32
322	Self-starting stretched-pulse fiber laser mode locked and stabilized with slow and fast semiconductor saturable absorbers. *Optics Letters*, **2001**, 26, 1809-11	3	32
321	Sub-Poissonian Narrowing of Length Distributions Realized in Ga-Catalyzed GaAs Nanowires. *Nano Letters*, **2017**, 17, 5350-5355	11.5	31
320	Observation of atomic ordering of triple-period-A and -B type in GaAsBi. *Applied Physics Letters*, **2014**, 105, 041602	3.4	31
319	High-power and broadly tunable GaSb-based optically pumped VECSELs emitting near 2 μm. *Journal of Crystal Growth*, **2009**, 311, 1917-1919	1.6	31
318	Temperature-stable operation of a quantum dot semiconductor disk laser. *Applied Physics Letters*, **2008**, 93, 051104	3.4	31
317	Mode-locked Bi-doped fiber laser. *Journal of the Optical Society of America B: Optical Physics*, **2007**, 24, 1807	1.7	31
316	11 W single gain-chip dilute nitride disk laser emitting around 1180 nm. *Optics Express*, **2010**, 18, 25633-41	3.3	30
315	Nanoimprint lithography patterned GaAs templates for site-controlled InAs quantum dots. *Journal of Crystal Growth*, **2011**, 323, 183-186	1.6	30
314	2.7 W tunable orange-red GaInNAs semiconductor disk laser. *Optics Express*, **2007**, 15, 18345-50	3.3	30
313	High-speed resonant cavity light-emitting diodes at 650 nm. *IEEE Journal of Selected Topics in Quantum Electronics*, **2002**, 8, 219-230	3.8	30
312	Field Emission from Self-Catalyzed GaAs Nanowires. *Nanomaterials*, **2017**, 7,	5.4	29
311	High power frequency doubled GaInNAs semiconductor disk laser emitting at 615 nm. *Optics Express*, **2007**, 15, 3224-9	3.3	29

310	Performance assessment of multijunction solar cells incorporating GaInNAsSb. *Nanoscale Research Letters*, **2014**, 9, 61	5	28
309	Picosecond passively mode-locked GaSb-based semiconductor disk laser operating at 2 μm. *Optics Letters*, **2010**, 35, 4090-2	3	28
308	MBE grown GaInNAs-based multi-Watt disk lasers. *Journal of Crystal Growth*, **2009**, 311, 1868-1871	1.6	28
307	Harmonically mode-locked VECSELs for multi-GHz pulse train generation. *Optics Express*, **2007**, 15, 955-64	3.3	28
306	Lithography-free oxide patterns as templates for self-catalyzed growth of highly uniform GaAs nanowires on Si(111). *Nanotechnology*, **2015**, 26, 275301	3.4	27
305	87 fs mode-locked Tm,Ho:CaYAlO laser at ~2043 nm. *Optics Letters*, **2018**, 43, 915-918	3	27
304	Spontaneous formation of three-dimensionally ordered Bi-rich nanostructures within GaAs1-x Bi x /GaAs quantum wells. *Nanotechnology*, **2016**, 27, 325603	3.4	27
303	Influence of As/group-III flux ratio on defects formation and photovoltaic performance of GaInNAs solar cells. *Solar Energy Materials and Solar Cells*, **2016**, 149, 213-220	6.4	26
302	High-efficiency GaInP/GaAs/GaInNAs solar cells grown by combined MBE-MOCVD technique. *Progress in Photovoltaics: Research and Applications*, **2016**, 24, 914-919	6.8	26
301	Evidence of Optical Circular Dichroism in GaAs-Based Nanowires Partially Covered with Gold. *Advanced Optical Materials*, **2017**, 5, 1601063	8.1	25
300	Spontaneous formation of nanostructures by surface spinodal decomposition in GaAs1−xBix epilayers. *Journal of Applied Physics*, **2015**, 117, 185302	2.5	25
299	Mode-locked VECSEL emitting 5 ps pulses at 675 nm. *Optics Letters*, **2013**, 38, 2289-91	3	25
298	Photo-acoustic spectroscopy revealing resonant absorption of self-assembled GaAs-based nanowires. *Scientific Reports*, **2017**, 7, 2833	4.9	24
297	Diode-pumped mode-locked Tm:LuAG laser at 2 μm based on GaSb-SESAM. *Optics Letters*, **2017**, 42, 839-842	3	23
296	Circular polarization switching and bistability in an optically injected 1300 nm spin-vertical cavity surface emitting laser. *Applied Physics Letters*, **2015**, 106, 021117	3.4	23
295	Large array of single, site-controlled InAs quantum dots fabricated by UV-nanoimprint lithography and molecular beam epitaxy. *Nanotechnology*, **2012**, 23, 175701	3.4	23
294	High-power disk lasers based on dilute nitride heterostructures. *New Journal of Physics*, **2009**, 11, 125019	2.9	23
293	Tunable modelocked bismuth-doped soliton fibre laser. *Electronics Letters*, **2008**, 44, 1456	1.1	23

292	Long-wavelength fast semiconductor saturable absorber mirrors using metamorphic growth on GaAs substrates. *Applied Physics Letters*, **2005**, 87, 121106	3.4	23
291	Broadly tunable mode-locked Ho:YAG ceramic laser around 2.1 μm. *Optics Express*, **2016**, 24, 18003-12	3.3	23
290	Broadband semiconductor saturable absorber mirrors in the 1.55-/spl mu/m wavelength range for pulse generation in fiber lasers. *IEEE Journal of Quantum Electronics*, **2002**, 38, 369-374	2	22
289	Characterization of InGaAs and InGaAsN semiconductor saturable absorber mirrors for high-power mode-locked thin-disk lasers. *Applied Physics B: Lasers and Optics*, **2012**, 106, 605-612	1.9	21
288	1180 nm VECSEL with output power beyond 20 W. *Electronics Letters*, **2013**, 49, 59-60	1.1	21
287	Te-doping of self-catalyzed GaAs nanowires. *Applied Physics Letters*, **2015**, 107, 012101	3.4	21
286	Pulse dynamics of a passively mode-locked Bi-doped fiber laser. *Optics Express*, **2010**, 18, 1041-8	3.3	21
285	Influence of deep level impurities on modulation response of InGaP light emitting diodes. *Journal of Applied Physics*, **2001**, 89, 1151-1155	2.5	21
284	Dynamics of time-resolved photoluminescence in GaInNAs and GaNAsSb solar cells. *Nanoscale Research Letters*, **2014**, 9, 80	5	20
283	Semiconductor Disk Lasers: Recent Advances in Generation of Yellow-Orange and Mid-IR Radiation. *Advances in Optical Technologies*, **2012**, 2012, 1-19		20
282	Structural and optical properties of InAs quantum dot chains grown on nanoimprint lithography structured GaAs with different pattern orientations. *Applied Physics Letters*, **2010**, 97, 173107	3.4	20
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280	Stretched-pulse fiber lasers based on semiconductor saturable absorbers. *Applied Physics B: Lasers and Optics*, **2002**, 74, s193-s200	1.9	20
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278	Optical Energy Transfer and Loss Mechanisms in Coupled Intracavity Light Emitters. *IEEE Transactions on Electron Devices*, **2016**, 63, 3567-3573	2.9	19
277	Broadband semiconductor saturable absorber mirror at 1.55 [micro sign]m using Burstein-Moss shifted Ga0.47In0.53As/InP distributed Bragg reflector. *Electronics Letters*, **2001**, 37, 374	1.1	19
276	Structural Investigation of Uniform Ensembles of Self-Catalyzed GaAs Nanowires Fabricated by a Lithography-Free Technique. *Nanoscale Research Letters*, **2017**, 12, 192	5	18
275	Size-dependent properties of single InAs quantum dots grown in nanoimprint lithography patterned GaAs pits. *Nanotechnology*, **2013**, 24, 235204	3.4	18

274	Absorption recovery dynamics in 2μm GaSb-based SESAMs. *Journal Physics D: Applied Physics*, **2014**, 47, 065102	3	18
273	Ab initio and scanning tunneling microscopy study of an indium-terminated GaAs(100) surface: An indium-induced surface reconstruction change in the c(8×2) structure. *Physical Review B*, **2010**, 81,	3.3	18
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271	Acidity sensor based on porphyrin self-assembled monolayers covalently attached to the surfaces of tapered fibres. *Measurement Science and Technology*, **2010**, 21, 115205	2	17
270	. *IEEE Journal of Selected Topics in Quantum Electronics*, **2008**, 14, 927-937	3.8	17
269	Stable single- and dual-wavelength fiber laser mode locked and spectrum shaped by a Fabry-Perot saturable absorber. *Optics Letters*, **2000**, 25, 1624-6	3	17
268	Temperature behaviour of resonant cavity light-emitting diodes at 650 nm. *Semiconductor Science and Technology*, **2000**, 15, 418-421	1.8	17
267	Identification of an isolated arsenic antisite defect in GaAsBi. *Applied Physics Letters*, **2014**, 104, 052110	3.4	16
266	Spectral narrowing and locking of a vertical-external-cavity surface-emitting laser using an intracavity volume Bragg grating. *IEEE Photonics Technology Letters*, **2006**, 18, 1786-1788	2.2	16
265	Femtosecond neodymium-doped fiber laser operating in the 894-909-nm spectral range. *IEEE Photonics Technology Letters*, **2004**, 16, 1029-1031	2.2	16
264	Detecting lateral composition modulation in dilute Ga(As,Bi) epilayers. *Nanotechnology*, **2015**, 26, 425701	3.4	15
263	Monolithic GaInNAsSb/GaAs VECSEL Operating at 1550 nm. *IEEE Journal of Selected Topics in Quantum Electronics*, **2015**, 21, 480-484	3.8	15
262	GaSb-based semiconductor saturable absorber mirrors for mode-locking 2 μm semiconductor disk lasers. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 294-297		15
261	1040 nm vertical external cavity surface emitting laser based on InGaAs quantum dots grown in Stranski-Krastanow regime. *Electronics Letters*, **2008**, 44, 290	1.1	15
260	High-power (>1 W) dilute nitride semiconductor disk laser emitting at 1240 nm. *New Journal of Physics*, **2007**, 9, 140-140	2.9	15
259	SESAM mode-locked Tm:LuYO ceramic laser generating 54-fs pulses at 2048 nm. *Applied Optics*, **2020**, 59, 10493-10497	1.7	15
258	Influence of nitrogen on hole effective mass and hole mobility in p-type modulation doped GaInNAs/GaAs quantum well structures. *Applied Physics Letters*, **2013**, 103, 082121	3.4	14
257	An analysis of Hall mobility in as-grown and annealed n- and p-type modulation-doped GaInNAs/GaAs quantum wells. *Nanoscale Research Letters*, **2012**, 7, 529	5	14

256	Light-trapping enhanced thin-film III-V quantum dot solar cells fabricated by epitaxial lift-off. *Solar Energy Materials and Solar Cells*, **2018**, 181, 83-92	6.4	13
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254	Optically Pumped Edge-Emitting GaAs-Based Laser With Direct Orange Emission. *IEEE Photonics Technology Letters*, **2014**, 26, 384-386	2.2	13
253	Magnetotransport study on as-grown and annealed n- and p-type modulation-doped GaInNAs/GaAs strained quantum well structures. *Nanoscale Research Letters*, **2014**, 9, 141	5	13
252	. *IEEE Photonics Technology Letters*, **2017**, 29, 114-117	2.2	13
251	Control of emitted light polarization in a 1310 nm dilute nitride spin-vertical cavity surface emitting laser subject to circularly polarized optical injection. *Applied Physics Letters*, **2014**, 105, 181106	3.4	13
250	Structural characterization of InAs quantum dot chains grown by molecular beam epitaxy on nanoimprint lithography patterned GaAs(100). *Nanotechnology*, **2011**, 22, 295604	3.4	13
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248	Narrow linewidth 1118/559 nm VECSEL based on strain compensated GaInAs/GaAs quantum-wells for laser cooling of Mg-ions. *Optical Materials Express*, **2012**, 2, 1011	2.6	13
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246	Study of nitrogen incorporation into GaInNAs: The role of growth temperature in molecular beam epitaxy. *Journal of Applied Physics*, **2012**, 112, 023504	2.5	13
245	Cascaded crystalline Raman lasers for extended wavelength coverage: continuous-wave, third-Stokes operation. *Optica*, **2018**, 5, 1406	8.6	13
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243	615 nm GaInNAs VECSEL with output power above 10 W. *Optics Express*, **2015**, 23, 20280-7	3.3	12
242	Determination of composition and energy gaps of GaInNAsSb layers grown by MBE. *Journal of Crystal Growth*, **2016**, 438, 49-54	1.6	12
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238	Te incorporation and activation as n-type dopant in self-catalyzed GaAs nanowires. *Physical Review Materials*, **2019**, 3,	3.2	12
237	Thermophotonic cooling in GaAs based light emitters. *Applied Physics Letters*, **2019**, 114, 051101	3.4	11
236	Oxidation of the GaAs semiconductor at the Al2O3/GaAs junction. *Physical Chemistry Chemical Physics*, **2015**, 17, 7060-6	3.6	11
235	Resonant Absorption in GaAs-Based Nanowires by Means of Photo-Acoustic Spectroscopy. *International Journal of Thermophysics*, **2018**, 39, 1	2.1	11
234	Dilute nitride triple junction solar cells for space applications: Progress towards highest AM0 efficiency. *Progress in Photovoltaics: Research and Applications*, **2018**, 26, 740-744	6.8	11
233	High Spectral Purity High-Power GaSb-Based DFB Laser Fabricated by Nanoimprint Lithography. *IEEE Photonics Technology Letters*, **2016**, 28, 1233-1236	2.2	11
232	High-power temperature-stable GaInNAs distributed Bragg reflector laser emitting at 1180 nm. *Optics Letters*, **2016**, 41, 657-60	3	11
231	Analytic modeling of temperature dependence of 2D carrier mobility in as-grown and annealed GaInNAs/GaAs quantum well structures. *Semiconductor Science and Technology*, **2014**, 29, 125009	1.8	11
230	Effects of (NH4)2S and NH4OH surface treatments prior to SiO2 capping and thermal annealing on 1.3 μm GaInAsN/GaAs quantum well structures. *Applied Physics Letters*, **2010**, 97, 111109	3.4	11
229	Properties of the SiO2- and SiNx-capped GaAs(100) surfaces of GaInAsN/GaAs quantum-well heterostructures studied by photoelectron spectroscopy and photoluminescence. *Applied Physics Letters*, **2011**, 99, 102105	3.4	11
228	Mode-Locked Bi-Doped All-Fiber Laser With Chirped Fiber Bragg Grating. *IEEE Photonics Technology Letters*, **2009**, 21, 599-601	2.2	11
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226	Optical switching in a resonant Fabry–Perot saturable absorber. *Journal of Optics*, **2006**, 8, 991-995		11
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224	Comparative study of defect levels in GaInNAs, GaNAsSb, and GaInNAsSb for high-efficiency solar cells. *Applied Physics Letters*, **2016**, 108, 122104	3.4	11
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220	Comparison of metal/polymer back reflectors with half-sphere, blazed, and pyramid gratings for light trapping in III-V solar cells. *Optics Express*, **2018**, 26, A331-A340	3.3	10
219	1.4 μm continuous-wave diamond Raman laser. *Optics Express*, **2017**, 25, 31377-31383	3.3	10
218	Unveiling and controlling the electronic structure of oxidized semiconductor surfaces: Crystalline oxidized InSb(100)(1 2)-O. *Physical Review B*, **2014**, 90,	3.3	10
217	Excitation energy-dependent nature of Raman scattering spectrum in GaInNAs/GaAs quantum well structures. *Nanoscale Research Letters*, **2012**, 7, 656	5	10
216	7.4 W yellow GaInNAs-based semiconductor disk laser. *Electronics Letters*, **2011**, 47, 1139	1.1	10
215	2-mu m Mode-Locked Semiconductor Disk Laser Synchronously Pumped Using an Amplified Diode Laser. *IEEE Photonics Technology Letters*, **2008**, 20, 1332-1334	2.2	10
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213	Intracavity Sum-Frequency Generation in Dual-Wavelength Semiconductor Disk Laser. *IEEE Photonics Technology Letters*, **2007**, 19, 1550-1552	2.2	10
212	Effects of heavy-ion and light-ion irradiation on the room temperature carrier dynamics of InGaAs/GaAs quantum wells. *Semiconductor Science and Technology*, **2006**, 21, 661-664	1.8	10
211	Comparison of single-side and double-side pumping of membrane external-cavity surface-emitting lasers. *Optics Letters*, **2019**, 44, 1146-1149	3	10
210	VECSEL systems for the generation and manipulation of trapped magnesium ions. *Optica*, **2016**, 3, 1294	8.6	10
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207	Analysis of GaAsBi growth regimes in high resolution with respect to As/Ga ratio using stationary MBE growth. *Journal of Crystal Growth*, **2019**, 511, 33-41	1.6	9
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202	Impact of the non-planar morphology of pre-patterned substrates on the structural and electronic properties of embedded site-controlled InAs quantum dots. *Journal of Applied Physics*, **2013**, 114, 174304	2.5	9
201	Comparison of thermal management techniques for semiconductor disk lasers **2008**,		9
200	Room temperature electron spin relaxation in GaInNAs multiple quantum wells at 1.3 μm. *Applied Physics Letters*, **2006**, 89, 211122	3.4	9
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196	AlGaAs-based vertical-external-cavity surface-emitting laser exceeding 4 W of direct emission power in the 740-790 nm spectral range. *Optics Letters*, **2018**, 43, 1578-1581	3	8
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194	AlGaAs/AlGaInP VECSELs With Direct Emission at 740–770 nm. *IEEE Photonics Technology Letters*, **2019**, 31, 1245-1248	2.2	8
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190	Formation and destabilization of Ga interstitials in GaAsN: Experiment and theory. *Physical Review B*, **2012**, 86,	3.3	8
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188	Dilute nitride vertical-cavity gate for all-optical logic at 1.3 μm. *IET Optoelectronics*, **2010**, 4, 201-209	1.5	8
187	Simultaneous Dual-Wavelength Conversion With Multiresonant Saturable Absorption Vertical-Cavity Semiconductor Gate. *IEEE Photonics Technology Letters*, **2008**, 20, 499-501	2.2	8
186	1 W at 617 nm generation by intracavity frequency conversion in semiconductor disk laser. *Electronics Letters*, **2007**, 43, 980	1.1	8
185	Power scaling and thermal lensing in 825 nm emitting membrane external-cavity surface-emitting lasers. *Optics Letters*, **2020**, 45, 547	3	8

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180	Removal of strain relaxation induced defects by flushing of InAs quantum dots. *Journal Physics D: Applied Physics*, **2012**, 45, 365107	3	7
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178	Harmonically mode-locked laser stabilized by semiconductor saturable absorber modulated with the residual pump. *Applied Physics B: Lasers and Optics*, **2002**, 75, 127-130	1.9	7
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